JCT151C-650RH 12A SCR

Rev.A.1.1

DESCRIPTION:

With high ability to withstand the shock loading of large current, JCT151C-650RH of silicon controlled rectifiers provides high dV

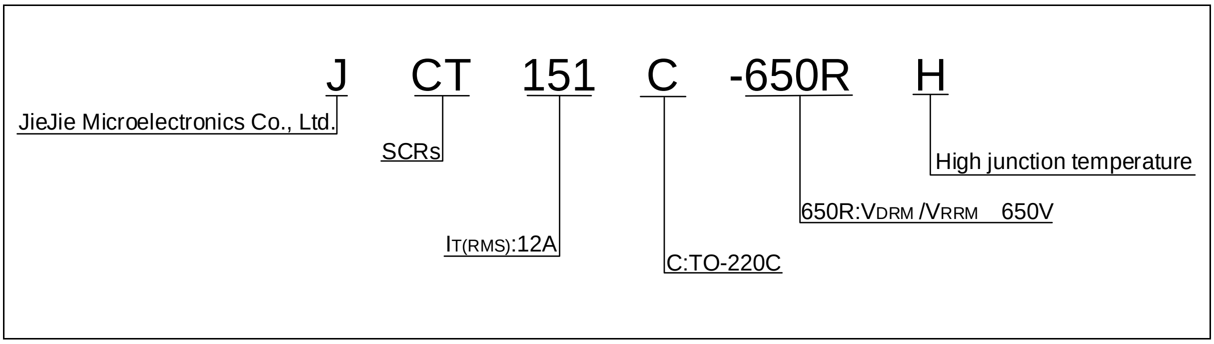
$_j$=150)	$P_{G(AV)}$	1	W
	$_{GM}$	10	W
$_j$=25 ; non-repetitive,off-state;FIG.7)	V_{pp}	0.7	kV

ELECTRICAL CHARACTERISTICS (T$_j$=25 unless otherwise specified)

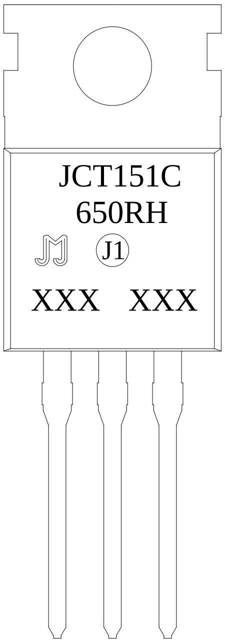
Symbol	Test Condition	Value			Unit
		MIN.	TYP.	MAX.	
I_{GT}	V_D=12V R_L=33	-	-	15	mA

V_{GT} .0 0 12 2C 12 0 5.2 0 0 12 201 12 0 -M1</MCI.16 (.0 0 12 2C 12 0 522.68 re (-)9 12 0 -MV 5.36.16 (.0 0 1-0.007 Tw 788 0.48 rTj

ORDERING INFORMATION



MARKING



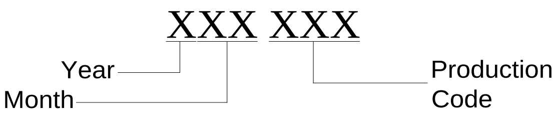


FIG.1: Maximum power dissipation versus RMS on-state current

FIG.2: RMS on-state current versus case temperature

FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards.